UNISONIC TECHNOLOGIES CO., LTD

UG40N120

Insulated Gate Bipolar Transistor

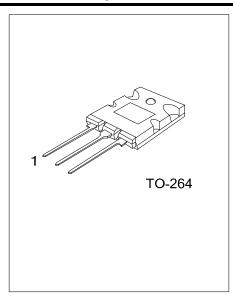
1200V NPT PLANAR IGBT

DESCRIPTION

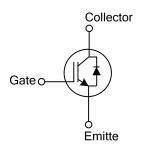
The UTC **UG40N120** is a 1200V NPT Planar Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to offers superior conduction and switching performance, high avalanche ruggedness and easy parallel operation.

■ FEATURES

- * High speed switching
- * High input impedance
- * Low saturation voltage: V_{CE(SAT)} =2.6V @ I_C=40A



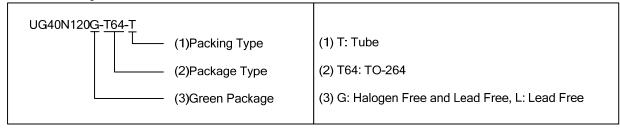
■ SYMBOL



ORDERING INFORMATION

Ordering Number		Dookone	Pin Assignment			Daakina	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UG40N120L-T64-T	UG40N120G-T64-T	TO-264	G	С	E	Tube	

Note: Pin Assignment: G: Gate D: Drain S: Source



■ MARKING



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■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V _{CES}	1200	V
Gate-Emitter Voltage		V_{GES}	±25	V
Continuous Collector Current	T _C =25°C	_	160	Α
	T _C =100°C	I _C	40	Α
Collector Current Pulsed (Note 1)		I _{CM}	160	Α
Diode Continuous Forward Current (T _C =100°C)		I _F	40	Α
Diode Maximum Forward Current	de Maximum Forward Current		160	Α
Power Dissipation		P_{D}	500	W
Operating Junction Temperature		TJ	-55 ~ +150	°C
Storage Temperature Range		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

■ THERMAL CHARACTERISTICS

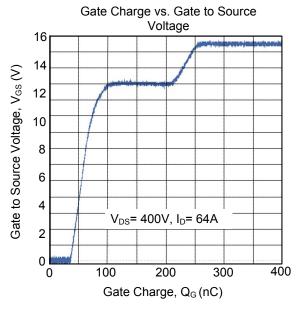
PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	θ_{JA}	25	°C/W	
Junction to Case	θ_{JC}	0.25	°C/W	

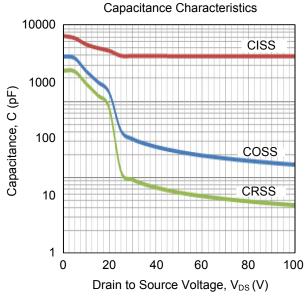
■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise noted)

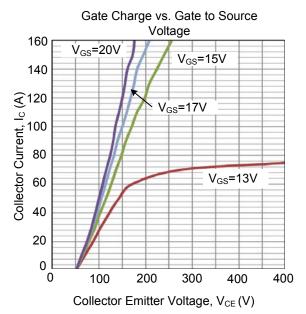
PARAMETER	SYMBOL	TEST CONDITIONS MII		MIN	TYP	MAX	UNIT
Off Characteristics							
Collector-Emitter Breakdown Voltage	B _{VCES}	I _C =1mA, V _{GE} =0V		1200			٧
Collector Cut-Off Current	I _{CES}	V _{CE} =V _{CES} , V _{GE} =0V				1	mΑ
G-E Leakage Current	I _{GES}	V _{GE} =V _{GES} , V _{CE} = 0V				±250	mA
On Characteristics							
Gate to Emitter Threshold Voltage	$V_{GE(TH)}$	$I_C=250\mu A, V_{CE}=V_{GE}$		3.5	5.5	7.5	V
Collector to Emitter Saturation Voltage	$V_{CE(SAT)}$	I _C =40A, V _{GE} =15V			2.2	2.6	V
Dynamic Characteristics							
Input Capacitance	C _{IES}	V _{CE} =30V, V _{GE} =0V, f=1MHz			4000		pF
Output Capacitance	C _{OES}				340		pF
Reverse Transfer Capacitance	C _{RES}			95		pF	
Switching Characteristics							
Turn-On Delay Time	t _{DON)}	V_{CC} =500V, I_{C} =64A, R_{G} =10 Ω , V_{GE} =10V			52		ns
Rise Time	t _R				106		ns
Turn-Off Delay Time	t _{DOFF)}				25		ns
Fall Time	t _F				64		ns
Total Gate Charge	Q_G				230		nC
Gate-Emitter Charge	Q_GE	V _{CE} =400V, I _C =64A, V _{GE} =15V			64		nC
Gate-Collector Charge	Q_GC				120		nC
SOURCE- DRAIN DIODE RATINGS AN		RISTICS					
Forward Voltage Drop	V _{FM}	I _F =40A	T _C =25°C		3.2	4.0	V
			T _C =125°C		2.7		V
Reverse Recovery Time	t _{rr}	I _F =30A,	T _C =25°C		460		ns
Reverse Recovery Charge	Q_{rr}	dI/dt=200A/μS	T _C =25°C		5		μC

^{2.} Pulse width limited by maximum junction temperature.

■ TYPICAL CHARACTERISTICS







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